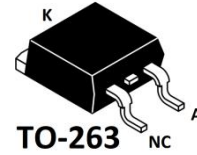


ESTF30A60SE

Super Fast Recovery Diode

Features

- Ultra fast Recovery Time
- Low Recovery Loss
- Low Forward Voltage
- Low Leakage Current



Applications

- Switching Power Supplies
- Snubber diode
- Anti parallel Diode for high frequency Switching Devices



Absolute Maximum Ratings @ T_c=25°C

Symbol	Parameter	ratings	Unit
V_{RRM}	Repetitive peak reverse voltage @50μA	600	V
V_{RWM}	Working Peak Reverse Voltage	600	V
I_{F(AV)}	Average forward current @T _c =110°C	30	A
I_{FSM}	Peak one Cycle Surge Forward @t=8.3ms	200	A
T_j	Junction Temperature	-55~+175	°C
T_{STG}	Storage temperature range	-55~+175	°C

Electrical Specifications @ T_c=25°C

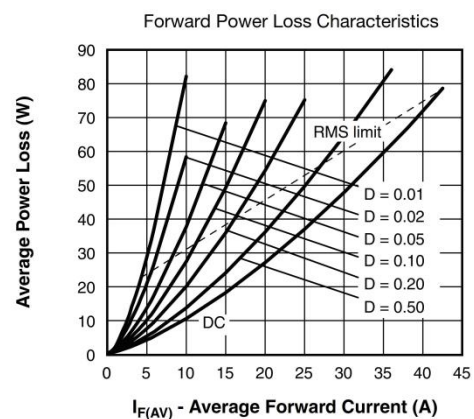
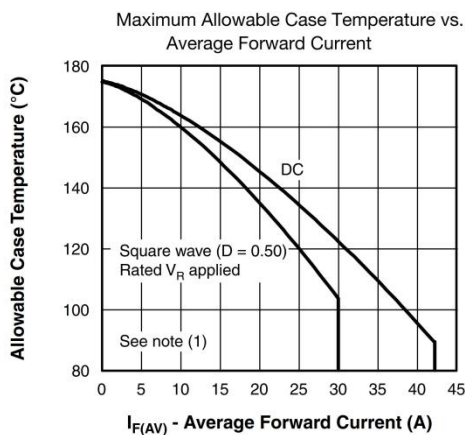
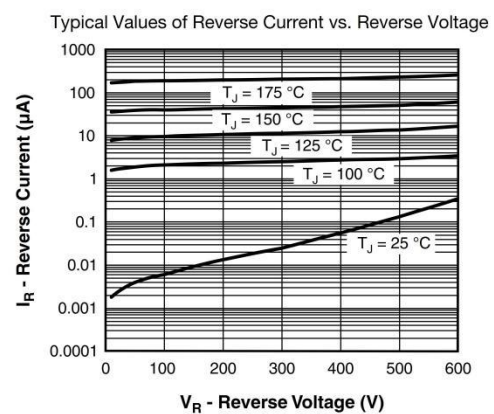
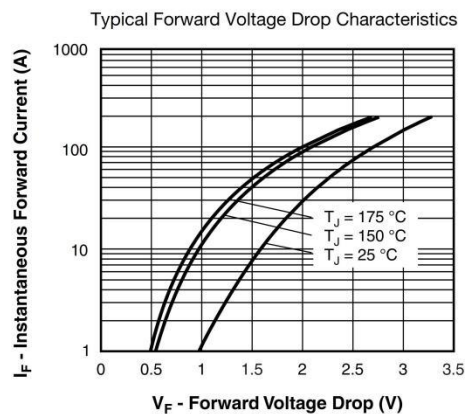
Symbol	Parameter		Ratings			Unit
			Min	Typ	Max	
I _R	T _j =25℃	V _R =V _{RRM}		0.3	50	μA
	T _j =125℃			65	500	μA
V _F	T _j =25℃	I _F =30A		2.0	2.5	V
	T _j =125℃				2.1	V
T _{rr}	I _F =0.5A, I _R =1A, I _{RR} =0.25A			28	40	ns
T _{rr}	I _F =30A, V _R =200V, di _F /dt=-200A/μs @T _C =25℃			30		ns
Q _{rr}				68		nC
I _{RRM}				3.5		A
T _{rr}	I _F =30A, V _R =200V, di _F /dt=-200A/μs			80		ns

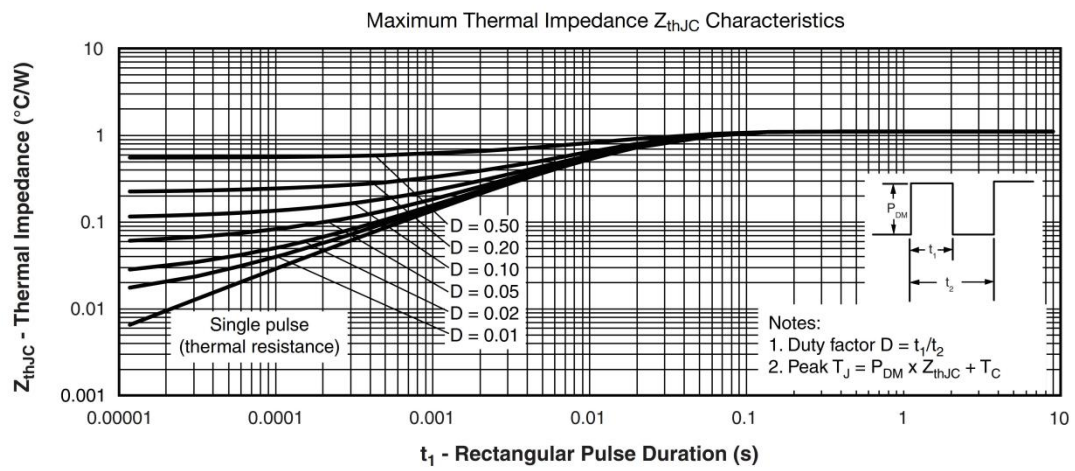
Q_{rr}	@T _c =125°C		260		nC
I_{RRM}			7		A
$R_{th(j-c)}$	Thermal resistance from junction to case	TO-247AC/ TO-263	0.2		°C/W

Order Message

Order codes	Package	Packaging
ESTF30A60SE	TO-263	Taping

Typical Performance Curves





Package